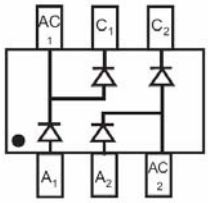
SOT-363 Plastic-Encapsulate Diodes

BAV99BRW SWITCHING DIODE

SOT-363



FEATURES

- Fast Switching Speed
- Ultra-Small Surface Mount Package
- For General Purpose Switching Applications
- High Conductance

MAKING: KGJ

Maximum Ratings @T_A=25℃

Parameter	Symbol	Limits	Unit
Peak Repetitive Peak reverse voltage **Working Peak Reverse Voltage** **DC Blocking Voltage**	V_{RRM} V_{RWM} V_R	75	V
Forward Continuous Current	I_{FM}	300	mA
Average Rectified Output Current	I_O	150	mA
Non-Repetitive Peak Forward Surge Current @ t = 1.0 us **@ t = 1.0s**	I_{FSM}	2 1	A
Power Dissipation	P_D	200	mW
Thermal Resistance Junction to Ambient Air	$R_{\theta JA}$	625	℃/W
Operating Junction Temperature	T_J	150	℃
Storage temperature	T_{STG}	-65-150	℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)R}$	I_R= 2.5 uA	75		V
Reverse voltage leakage current	I_R	V_R=75V V_R=20V		2.5 0.025	uA
Forward voltage	V_F	I_F=1mA I_F=10mA I_F=50mA I_F=150mA		715 855 1000 1250	mV
Junction capacitance	C_T	V_R=0, f=1MHz		2	pF
Reveres recovery time	t_{rr}	I_F=I_R=10mA,I_{rr}=0.1XI_R, R_L=100Ω		4	nS

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Typical Characteristics

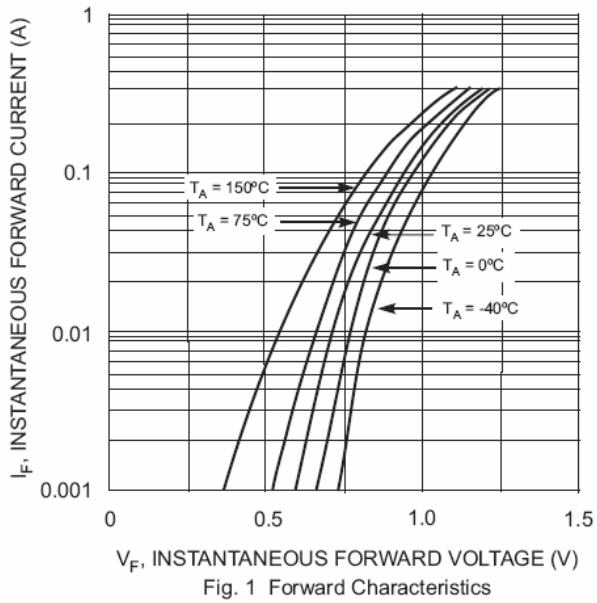

Fig. 1 Forward Characteristics

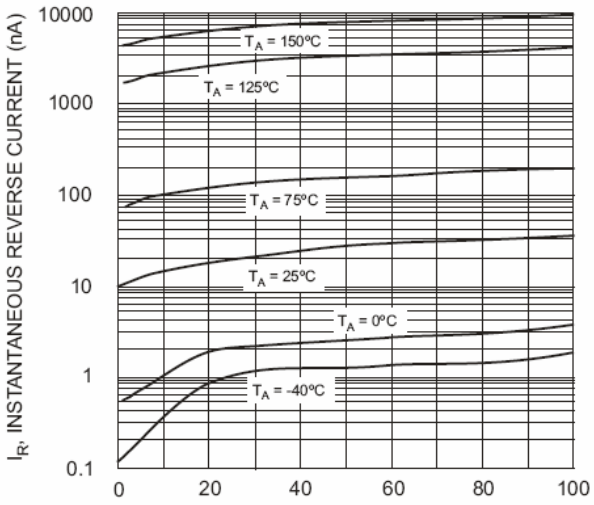

Fig. 2 Typical Reverse Characteristics

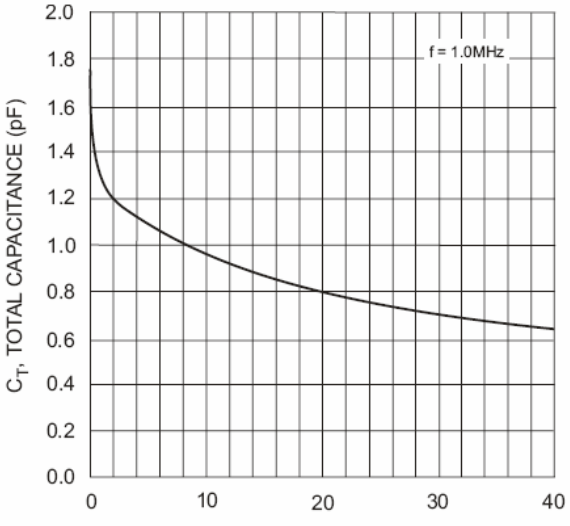

Fig. 3 Typical Capacitance vs. Reverse Voltage

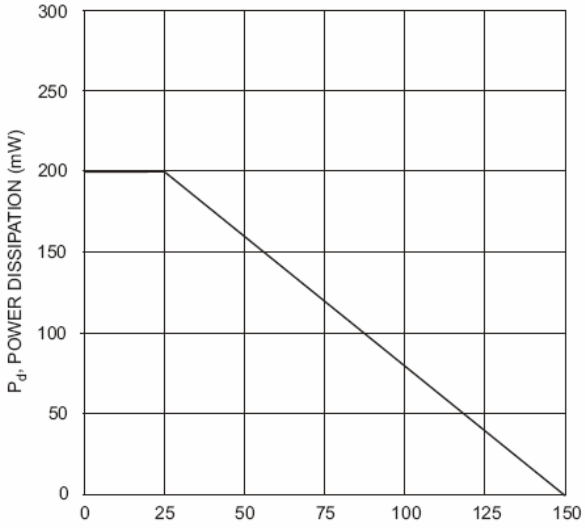

Fig. 4 Power Derating Curve, Note 1